

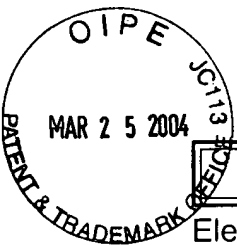


Electronic Filing System (EFS) Data  
Electronic Patent Application Submission  
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EFS ID: 57874  
Application ID: 10722792   
Title of Invention: Method of Fabricating a High-Voltage Transistor With A Multi-Layered Extended Drain Structure  
First Named Inventor: Donald Disney  
Domestic/Foreign Application: Domestic Application  
Filing Date: 2003-11-25  
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Confirmation number: 7244  
Attorney Docket Number: 03692.P059DC


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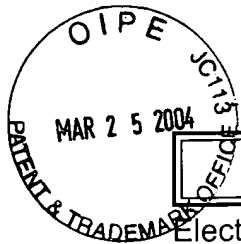
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TRANSMITTAL

Electronic Version v1.1  
Stylesheet Version v1.1.0

Title of Invention	Method of Fabricating a High-Voltage Transistor With A Multi-Layered Extended Drain Structure									
Application Number: 10/722792 										
Date: 2003-11-25										
First Named Applicant: Donald Ray Disney										
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Attorney Docket Number: 03692.P059DC										
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<table border="1"><thead><tr><th>Submitted by:</th><th>Elec. Sign.</th><th>Sign. Capacity</th></tr></thead><tbody><tr><td>Bradley John Berezna Registered Number: 33,474</td><td>BJB</td><td>Attorney</td></tr></tbody></table>			Submitted by:	Elec. Sign.	Sign. Capacity	Bradley John Berezna Registered Number: 33,474	BJB	Attorney		
Submitted by:	Elec. Sign.	Sign. Capacity								
Bradley John Berezna Registered Number: 33,474	BJB	Attorney								
<table><tr><td>Documents being submitted</td><td>Files</td></tr><tr><td>us-ids</td><td>03692.P059DC-usidst.xml</td></tr><tr><td></td><td>us-ids.dtd</td></tr><tr><td></td><td>us-ids.xsl</td></tr></table>			Documents being submitted	Files	us-ids	03692.P059DC-usidst.xml		us-ids.dtd		us-ids.xsl
Documents being submitted	Files									
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	us-ids.dtd									
	us-ids.xsl									
Comments										



## ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of  
Invention

Method of Fabricating a High-Voltage Transistor With A  
Multi-Layered Extended Drain Structure

Application Number: 10/722792



Confirmation Number: 7244

First Named Applicant: Donald Disney

Attorney Docket Number: 03692.P059DC

Art Unit: 2818

Examiner: David Nhu

Search string: ( 6184555 or 6462377 or 6127703 or 5306656  
or 6525372 or 6468847 or 5973360 or 5637898  
or 5665994 or 4929987 or 4531173 or 6573558  
or 6555873 or 6509220 or 6667213 or 6635544  
or 6365932 or 4626789 or 6294818 or 5760440  
or 6049108 or 5821144 or 4738936 or 5869875  
or 6191447 or 4343015 or 6388286 or 6194283  
or 4890144 or 6353252 or 6207994 or 5155574  
or 5146298 or 4811075 or 4626879 or 4890146  
or 5237193 or 5368136 or 5313082 or 5068700  
or 5258636 or 20020175351 or 20020056884 or  
20010015459 ).pn.

### US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

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	2	6462377	2002-10-08	Hurky et al.	B2		
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Note: Applicant is not required to submit a paper copy of cited US Published Applications

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	2	20020056884	2002-05-16	Baliga	A1		
	3	20010015459	2001-08-23	Watanabe et al.	A1		

Signature

Examiner Name	Date